

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: 1N5820RL
Manufacturer: STMicroelectronics
Package: DO-201AD, Axial
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/stmicroelectronics/1n5820rl.html>

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

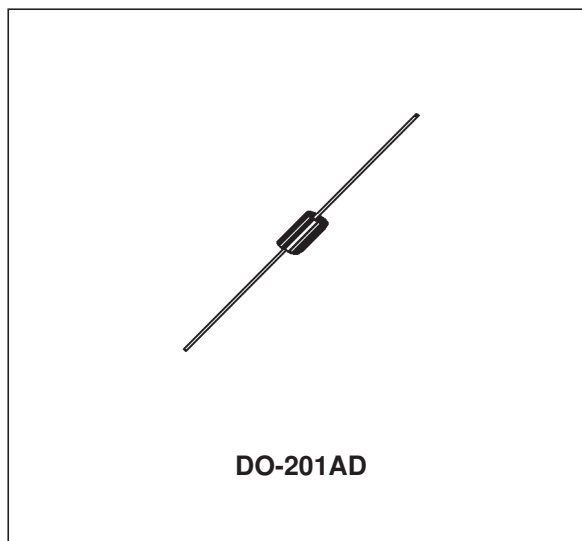
$I_{F(AV)}$	3 A
V_{RRM}	40 V
T_j	150°C
$V_F(max)$	0.475 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Axial Power Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters. Packaged in DO-201AD these devices are intended for use in low voltage, high frequency inverters, free wheeling, polarity protection and small battery chargers.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value			Unit
			1N5820	1N5821	1N5822	
V_{RRM}	Repetitive peak reverse voltage		20	30	40	V
$I_{F(RMS)}$	RMS forward current		10			A
$I_{F(AV)}$	Average forward current	$T_L = 100^\circ\text{C} \quad \delta = 0.5$			3	A
		$T_L = 110^\circ\text{C} \quad \delta = 0.5$	3	3		A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	80			A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s} \quad T_j = 25^\circ\text{C}$	1700			W
T_{stg}	Storage temperature range		- 65 to + 150			°C
T_j	Maximum operating junction temperature *		150			°C
dV/dt	Critical rate of rise of reverse voltage		10000			V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

1N582x

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-a)}$	Junction to ambient	Lead length = 10 mm	80	°C/W
$R_{th(j-l)}$	Junction to lead	Lead length = 10 mm	25	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		1N5820	1N5821	1N5822	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	2	2	2	mA
		$T_j = 100^\circ\text{C}$		20	20	20	mA
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 3\text{ A}$	0.475	0.5	0.525	V
		$T_j = 25^\circ\text{C}$	$I_F = 9.4\text{ A}$	0.85	0.9	0.95	V

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equations :

$P = 0.33 \times I_{F(AV)} + 0.035 I_{F(RMS)}^2$ for 1N5820 / 1N5821

$P = 0.33 \times I_{F(AV)} + 0.060 I_{F(RMS)}^2$ for 1N5822

Fig. 1: Average forward power dissipation versus average forward current (1N5820/1N5821).

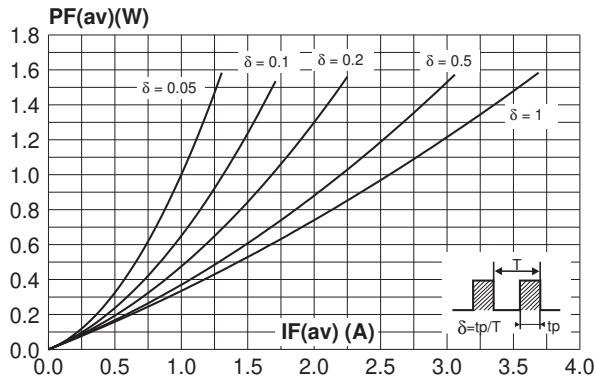


Fig. 3: Normalized avalanche power derating versus pulse duration.

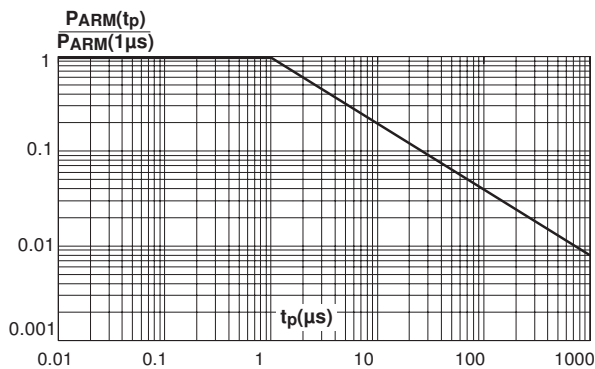


Fig. 2: Average forward power dissipation versus average forward current (1N5822).

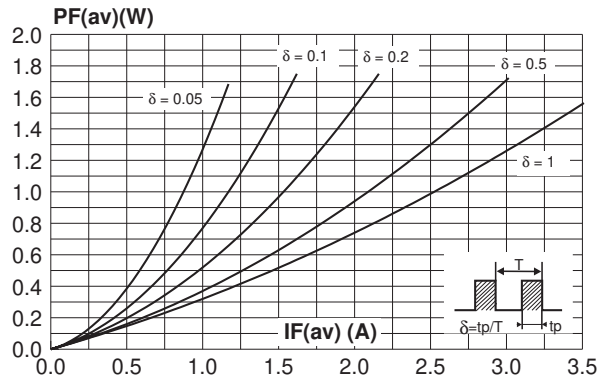


Fig. 4: Normalized avalanche power derating versus junction temperature.

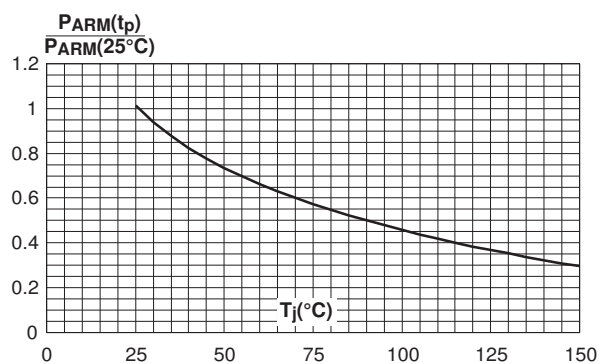


Fig. 5-1: Average forward current versus ambient temperature ($\delta=0.5$) (1N5820/1N5821).

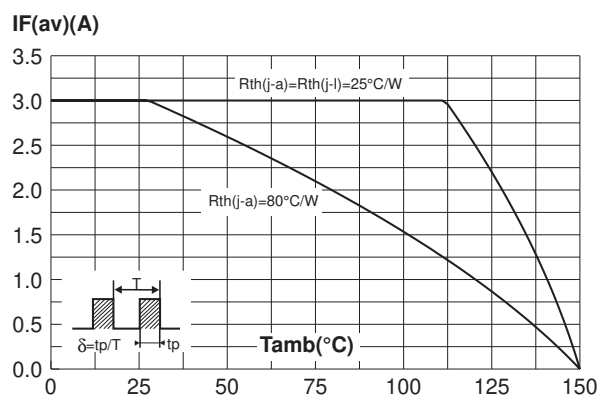


Fig. 5-2: Average forward current versus ambient temperature ($\delta=0.5$) (1N5822).

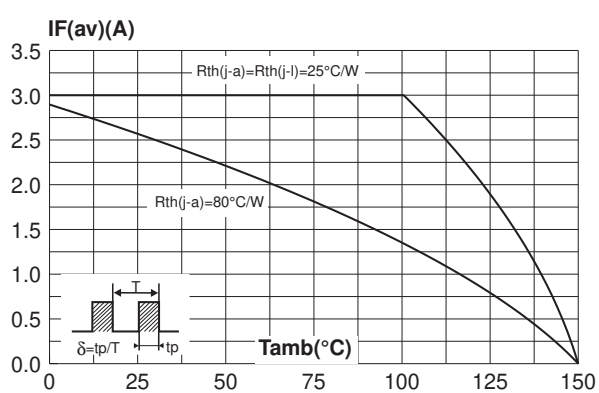


Fig. 6-1: Non repetitive surge peak forward current versus overload duration (maximum values) (1N5820/1N5821).

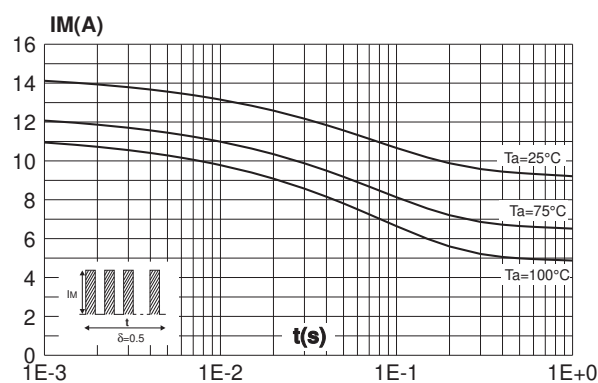


Fig. 6-2: Non repetitive surge peak forward current versus overload duration (maximum values) (1N5822).

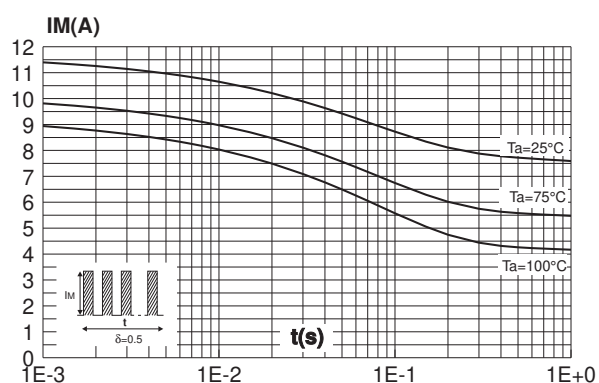


Fig. 7: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, $e(\text{Cu})=35\text{mm}$, recommended pad layout).

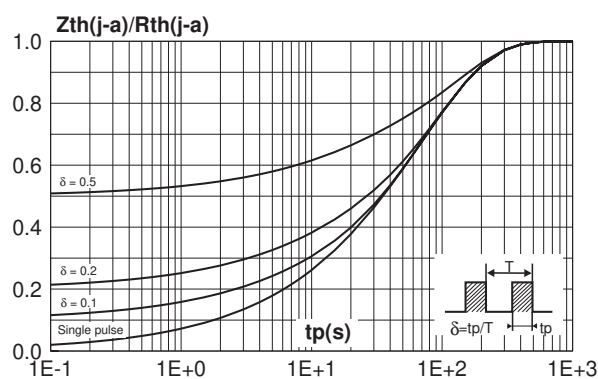


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

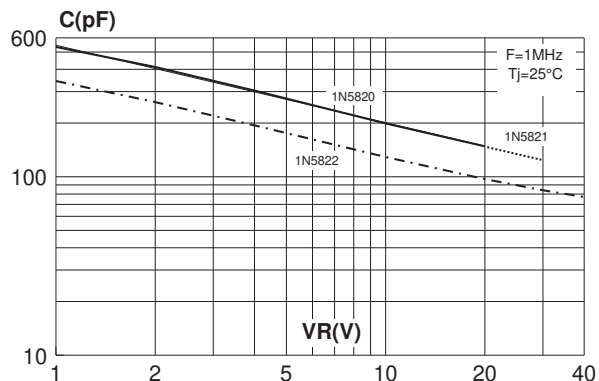


Fig. 9-1: Reverse leakage current versus reverse voltage applied (typical values) (1N5820/1N5821).

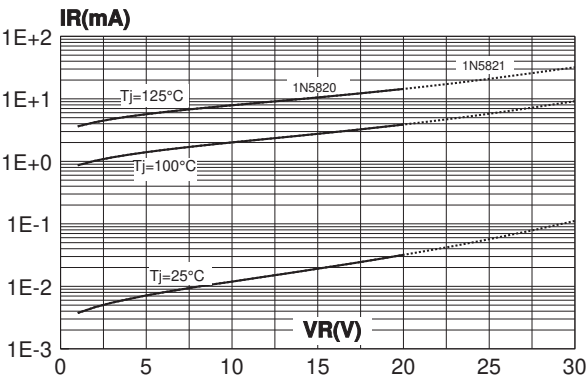


Fig. 9-2: Reverse leakage current versus reverse voltage applied (typical values) (1N5822).

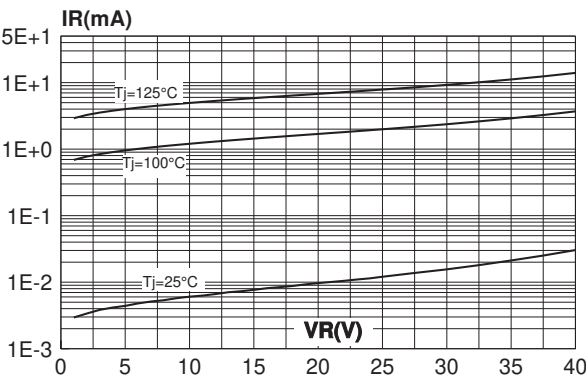


Fig. 10-1: Forward voltage drop versus forward current (typical values) (1N5820/1N5821).

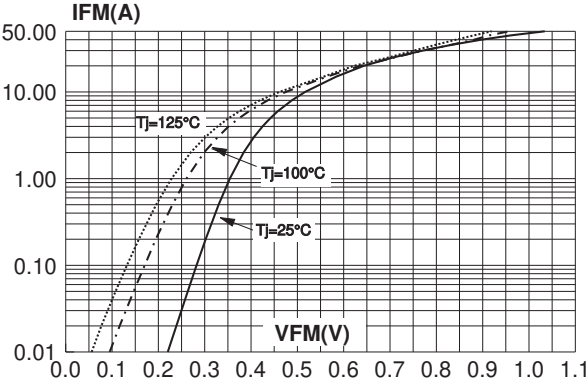


Fig. 10-2: Forward voltage drop versus forward current (typical values) (1N5822).

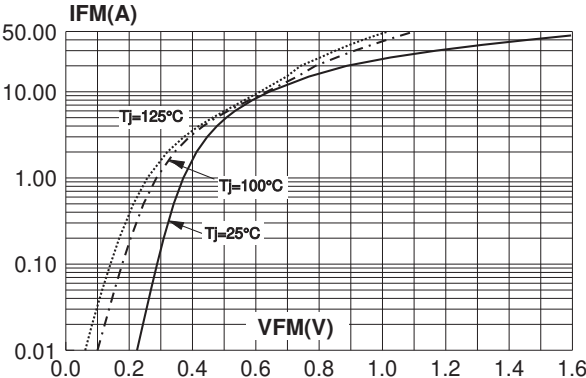
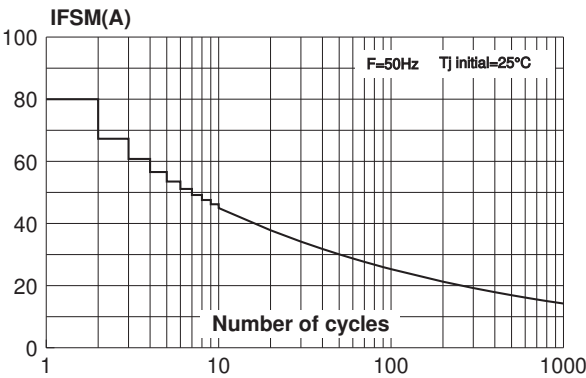
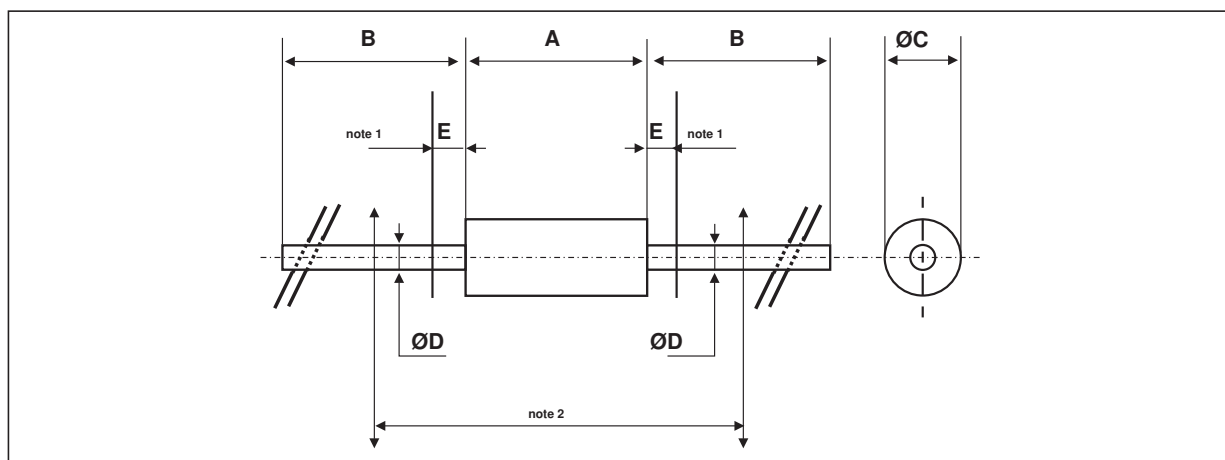


Fig. 11: Non repetitive surge peak forward current versus number of cycles.



PACKAGE MECHANICAL DATA

DO-201AD plastic



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A		9.50		0.374	1 - The lead diameter ♠ D is not controlled over zone E 2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)
B	25.40		1.000		
♠ C		5.30		0.209	
♠ D		1.30		0.051	
E		1.25		0.049	

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
1N582x	Part number cathode ring	DO-201AD	1.12g	600	Ammopack
1N582xRL	Part number cathode ring	DO-201AD	1.12g	1900	Tape & reel

• EPOXY MEETS UL94,V0

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